

HIGH-SPEED 4K x 8 DUAL-PORT STATIC SRAM

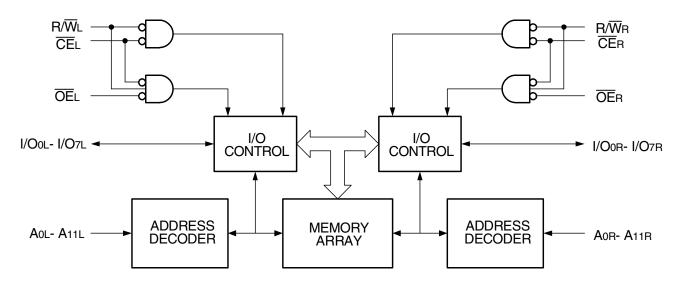
7134SA/LA

Features

- High-speed access
 - Commercial: 20/55ns (max.)
 - Industrial: 25ns (max.)
 - Military: 35/45/55/70ns (max.)
- Low-power operation
 - *IDT7134SA*
 - Active: 700mW (typ.) Standby: 5mW (typ.)
 - IDT7134LA
 - Active: 700mW (typ.) Standby: 1mW (typ.)

- Fully asynchronous operation from either port
- Battery backup operation—2V data retention (LA only)
- ◆ TTL-compatible; single 5V (±10%) power supply
- Available in 48-pin DIP, LCC, Flatpack and 52-pin PLCC
- ◆ Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



2720 drw 01

Description

The IDT7134 is a high-speed 4K x 8 Dual-Port Static RAM designed to be used in systems where on-chip hardware port arbitration is not needed. This part lends itself to those systems which cannot tolerate wait states or are designed to be able to externally arbitrate or withstand contention when both sides simultaneously access the same Dual-Port RAM location.

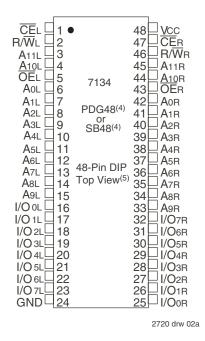
The IDT7134 provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. It is the user's responsibility to ensure data integrity when simultaneously accessing the same memory location from both ports. An automatic power down feature,

controlled by \overline{CE} , permits the on-chip circuitry of each port to enter a very low standby power mode.

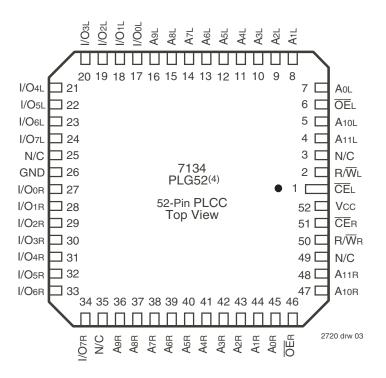
Fabricated using CMOS high-performance technology, these Dual-Ports typically operate on only 700mW of power. Low-power (LA) versions offer battery backup data retention capability, with each port typically consuming 200µW from a 2V battery.

The IDT7134 is packaged in either a sidebraze or plastic 48-pin DIP, 48-pin LCC, 52-pin PLCC and 48-pin Flatpack. Military grade product is manufactured in compliance with MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

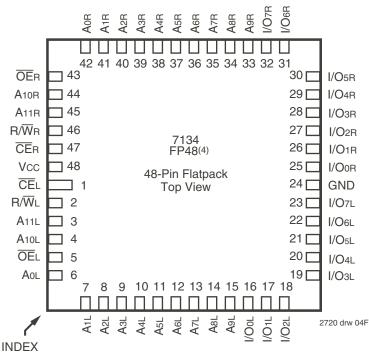
Pin Configurations (1,2,3)

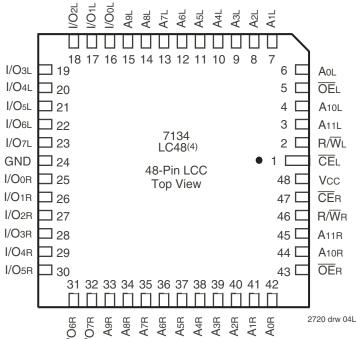


- 1. All Vcc pins must be connected to the power supply.
- All GND pins must be connected to the ground supply.
- PDG48 package body is approximately .55 in x 2.43 in x .18 in. SB48 package body is approximately .62 in x 2.43 in x .15 in. PLG52 package body is approximately .75 in x .75 in x .17 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of actual part-marking.



Pin Configurations (1,2,3)(con't.)





- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. LC48 package body is approximately .57 in x .57 in x .68 in. FP48 package body is approximately .75 in x .75 in x .11 in.
- 4. This package code is used to reference the package diagram.

Absolute Maximum Ratings(1)

			<u> </u>	
Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tstg	Storage Temperature	-65 to +150	-65 to +150	°C
PT ⁽³⁾	Power Dissipation	1.5	1.5	W
ЮИТ	DC Output Current	50	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may
 cause permanent damage to the device. This is a stress rating only and functional
 operation of the device at these or any other conditions above those indicated in the
 operational sections of this specification is not implied. Exposure to absolute
 maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10 ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc +10%.
- 3. VTERM = 5.5V.

NOTES:

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	11	pF
Соит	Output Capacitance	Vout = 3dV	11	pF

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- 1. This parameter is determined by device characterization but is not production tested.
- 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V and from 3V to 0V.

Recommended Operating Temperature and Supply Voltage^(1,2)

romporar		79.5	· orrage
Grade	Ambient Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

NOTES:

- 1. VIL (min.) \geq -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($Vcc = 5V \pm 10\%$)

	1 3 0 0							
			7134SA		713			
Symbol	Parameter	Test Conditions	Min.	Мах.	Min.	Max.	Unit	
Iu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $Vin = 0V$ to Vcc	_	10	-	5	μΑ	
ILO	Output Leakage Current	\overline{CE} - Vih, Vout = 0V to Vcc	-	10	ı	5	μΑ	
Vol	Output Low Voltage	IoL = 6mA	-	0.4	ı	0.4	٧	
		IoL = 8mA	_	0.5	_	0.5	V	
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	V	

NOTES:

1. At Vcc ≤ 2.0V input leakages are undefined.

2720 tbl 05

2720 thl 03

2720 tbl 04

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,2)}$ (Vcc = 5.0V \pm 10%)

								IX20 Only		4X25 & Ind	Co	1X35 m'l litary	
Symbol	Parameter	Test Condition	Versio	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit		
Icc	Dynamic Operating Current (Both Ports Active)	CE = VIL Outputs Disabled f = fwax ⁽³⁾	COM'L	SA LA	170 170	280 240	160 160	280 220	150 150	260 210	mA		
		I = IMAX*	MIL & IND	SA LA	_	_	160 160	310 260	150 150	300 250			
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{\text{CE}}_L$ and $\overline{\text{CE}}_R = \text{VIH}$ $f = \text{fMAX}^{(3)}$	COM'L	SA LA	25 25	100 80	25 25	80 50	25 25	75 45	mA		
	Lever inpuis)		MIL & IND	SA LA			25 25	100 80	25 25	75 55			
ISB2	Standby Current (One Port - TTL	$\overline{\mathbb{CE}}$ -A" = VIL and $\overline{\mathbb{CE}}$ -B" = VIH Active Port Outputs Disabled, $f=f_{MAX}^{(3)}$	COM'L	SA LA	105 105	180 150	95 95	180 140	85 85	170 130	mA		
	Level Inputs)	I=IMAX [©]	MIL & IND	SA LA			95 95	210 170	85 85	200 160			
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports CEL and CER ≥ Vcc - 0.2V VM > Vcc - 0.2V or	COM'L	SA LA	1.0 0.2	15 4.5	1.0 0.2	15 4.0	1.0 0.2	15 4.0	mA		
	Civios Level lipus)	$V_{\text{IN}} \le V_{\text{CC}} = 0.2V_{\text{O}}$ of $V_{\text{IN}} \le 0.2V_{\text{O}}$, $f = 0^{(3)}$	MIL & IND	SA LA			1.0 0.2	30 10	1.0 0.2	30 10			
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	One Port \overline{CE} 'a" or \overline{CE} 'B" \geq Vcc - 0.2V VN \geq Vcc - 0.2V or VN \leq 0.2V	COM'L	SA LA	105 105	170 130	95 95	170 120	85 85	160 110	mA		
	TOWOS Lever Ilipuis)	Active Port Outputs Disabled, $f = f_{MAX}^{(3)}$	MIL & IND	SA LA			95 95	210 150	85 85	190 130			

2720 tbl 06a

					Con	4X45 n'l & itary	Com'	4X55 I, Ind litary	Con	IX70 n'I & tary	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CE = VIL Outputs Disabled f = fmax ⁽³⁾	COM'L	SA LA	140 140	240 200	140 140	240 200	140 140	240 200	mA
	(DOIN FORS ACTIVE)	I = IMAX**	MIL & IND	SA LA	140 140	280 240	140 140	270 220	140 140	270 220	
ISB1	Standby Current (Both Ports - TTL	\overline{CE} L and \overline{CE} R = VIH f = f MAX ⁽³⁾	COM'L	SA LA	25 25	70 40	25 25	70 40	25 25	70 40	mA
	Level Inputs)		MIL & IND	SA LA	25 25	70 50	25 25	70 50	25 25	70 50	
ISB2	Standby Current (One Port - TTL	CE'a* = VIL and CE'β* = VIH Active Port Outputs Disabled, f=fmax ⁽³⁾	COM'L	SA LA	75 75	160 130	75 75	160 130	75 75	160 130	mA
	Level Inputs)	T=IMAX ^e ⁷	MIL & IND	SA LA	75 75	190 150	75 75	180 150	75 75	180 150	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports CEL and CER ≥ Vcc - 0.2V VN > Vcc - 0.2V or	COM'L	SA LA	1.0 0.2	15 4.0	1.0 0.2	15 4.0	1.0 0.2	15 4.0	mA
	Civios Level Inpuis)	$V_{\text{IN}} \leq 0.2V, f = 0^{(3)}$	MIL & IND	SA LA	1.0 0.2	30 10	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	One Port \overline{CE}'' or $\overline{CE}'' > Vcc - 0.2V$ $VN \ge \overline{V}cc - 0.2V$ or $VN \le 0.2V$	COM'L	SA LA	75 75	150 100	75 75	150 100	75 75	150 100	mA
	TOWOS Level Inputs)	Active Port Outputs Disabled, $f = f_{MAX}^{(2)}$	MIL & IND	SA LA	75 75	180 120	75 75	170 120	75 75	170 120	

- 1. 'X' in part number indicates power rating (SA or LA).
- 2. Vcc = 5V, TA = +25°C for typical, and parameters are not production tested.
- 3. fMAX = 1/tRC = All inputs cycling at f = 1/tRC (except Output Enable). f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby ISB3.

Data Retention Characteristics Over All Temperature Ranges

(LA Version Only) VLC = 0.2V, VHC = VCC - 0.2V

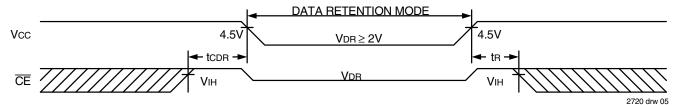
Symbol	Parameter	Test Condition	on	Min.	Typ. ⁽¹⁾	Max.	Unit
VDR	Vcc for Data Retention	Vcc = 2V	2.0		-	٧	
ICCDR	Data Retention Current	CE ≥ VHC MIL. & IND.		_	100	4000	μΑ
		VIN > VHC or < VLC	IN \geq VHC or \leq VLC COM'L.		100	1500	
tcdr ⁽³⁾	Chip Deselect to Data Retention Time			0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_	_	ns

2720 tbl 07

NOTES:

- 1. Vcc = 2V, TA = +25°C, and are not production tested.
- 2. trc = Read Cycle Time.
- 3. This parameter is guaranteed by device characterization, but not production tested.

Data Retention Waveform



AC Test Conditions

AC 1631 CONDITIONS	710 TCSL CONDITIONS								
Input Pulse Levels	GND to 3.0V								
Input Rise/Fall Times	5ns								
Input Timing Reference Levels	1.5V								
Output Reference Levels	1.5V								
Output Load	Figures 1 and 2								

2720 tbl 08

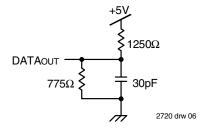


Figure 1. AC Output Test Load

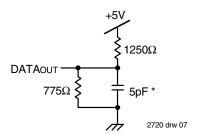


Figure 2. Output Test Load (for t.z, thz, twz, tow) *Including scope and jig

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽³⁾

			4X20 I Only		4X25 & Ind	7134X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	20	_	25	_	35	_	ns
taa	Address Access Time	_	20	_	25		35	ns
tace	Chip Enable Access Time	_	20	_	25		35	ns
taoe	Output Enable Access Time	_	15	_	15		20	ns
toн	Output Hold from Address Change	0	_	0	_	0	_	ns
tlz	Output Low-Z Time ^(1,2)	0	_	0	_	0	_	ns
tHZ	Output High-Z Time ^(1,2)	_	15	_	15		20	ns
tpu	Chip Enable to Power Up Time (2)	0	_	0		0	_	ns
tpd	Chip Disable to Power Down Time ⁽²⁾	_	20	_	25		35	ns

2720 tbl 09a

2720 tbl 09b

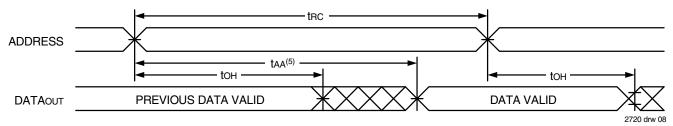
		Con	4X45 n'l & itary	Com'	1X55 I, Ind litary	Con	7134X70 Com'l & Military	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	45	_	55	_	70	_	ns
taa	Address Access Time	_	45	_	55	_	70	ns
tace	Chip Enable Access Time	_	45	_	55	_	70	ns
taoe	Output Enable Access Time	_	25	_	30	_	40	ns
tон	Output Hold from Address Change	0	_	0	_	0	_	ns
tLZ	Output Low-Z Time ^(1,2)	5	_	5	_	5	_	ns
tHZ	Output High-Z Time ^(1,2)	_	20	_	25	_	30	ns
tpu	Chip Enable to Power Up Time (2)	0	_	0	_	0	_	ns
tPD	Chip Disable to Power Down Time ⁽²⁾		45	_	50		50	ns

NOTES

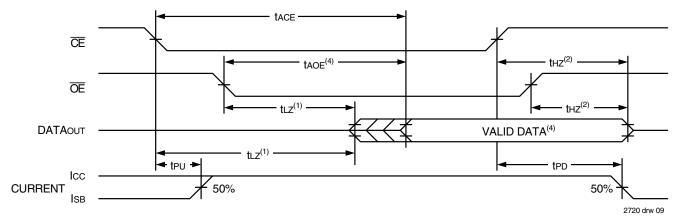
1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. 'X' in part number indicates power rating (SA or LA).

Timing Waveform of Read Cycle No. 1, Either Side(1,2,4)



Timing Waveform of Read Cycle No. 2, Either Side^(1,3)



- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R/\overline{W} = VIH$
- 4. Start of valid data depends on which timing becomes effective, taoe, tace or taa
- 5. taa for RAM Address Access and tsaa for Semaphore Address Access.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

		7134X20 Com'l Only		7134X25 Com'l & Ind		7134X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE	<u> </u>							
twc	Write Cycle Time	20		25	_	35		ns
tew	Chip Enable to End-of-Write	15		20	_	30		ns
taw	Address Valid to End-of-Write	15		20	_	30		ns
tas	Address Set-up Time	0	_	0	_	0	_	ns
twp	Write Pulse Width	15	_	20	_	25	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	15	_	15	_	20	_	ns
tHZ	Output High-Z Time ^(1,2)		15	_	15		20	ns
tон	Data Hold Time ⁽³⁾	0		0		3		ns
twz	Write Enable to Output in High-Z ^(1,2)	_	15		15		20	ns
tow	Output Active from End-of-Write ^(1,2,3)	3	_	3	_	3		ns
twdd	Write Pulse to Data Delay ⁽⁴⁾	_	40		50		60	ns
todo	Write Data Valid to Read Data Delay ⁽⁴⁾		30	_	30		35	ns

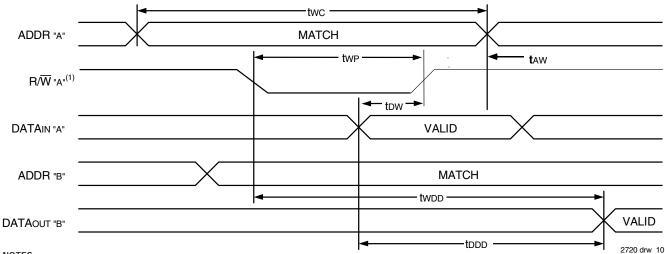
2720 tbl 10a

2720 tbl 10b

		7134X45 Com'l & Military		7134X55 Com'l, Ind & Military		7134X70 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time	45	_	55		70	_	ns
tew	Chip Enable to End-of-Write	40	_	50		60	_	ns
taw	Address Valid to End-of-Write	40	_	50		60	_	ns
tas	Address Set-up Time	0	_	0		0	_	ns
twp	Write Pulse Width	40	_	50		60		ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	20	_	25		30	_	ns
tHZ	Output High-Z Time ^(1,2)	T -	20	_	25	_	30	ns
tон	Data Hold Time ⁽³⁾	3	_	3		3		ns
twz	Write Enable to Output in High-Z ^(1,2)	_	20		25		30	ns
tow	Output Active from End-of-Write (1,2,3)	3	_	3		3		ns
twdd	Write Pulse to Data Delay ⁽⁴⁾		70		80		90	ns
todo	Write Data Valid to Read Data Delay ⁽⁴⁾		45		55		70	ns

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. The specification for toh must be met by the device supplying write data to the RAM under all operating conditions. Although toh and tow values will vary over voltage and temperature, the actual toh will always be smaller than the actual tow.
- 4. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read".
- 5. 'X' in part number indicates power rating (SA or LA).

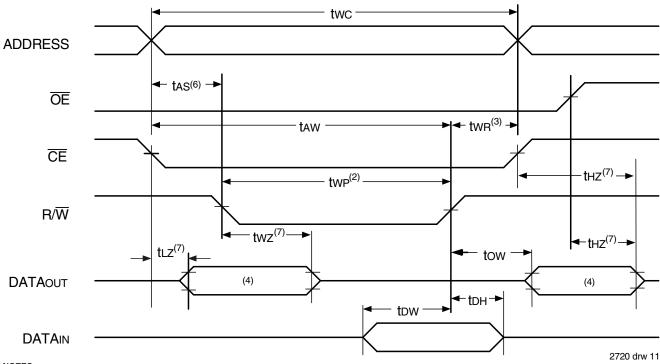
Timing Waveform of Write with Port-to-Port Read(1,2,3)



NOTES:

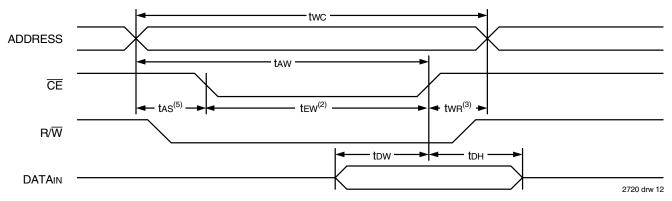
- 1. Write cycle parameters should be adhered to, in order to ensure proper writing.
- 2. $\overline{CE}L = \overline{CE}R = VIL$. \overline{OE} "B" = VIL.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing (1,5,8)



- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} =VIL and R/ \overline{W} = VIL.
- 3. two is measured from the earlier of \overline{CE} or R/\overline{W} going to ViH to the end-of-write cycle.
- 4. During this period, the I/O pins are in the output state, and input signals must not be applied.
- 5. If the $\overline{CE} = V_{IL}$ transition occurs simultaneously with or after the $R/\overline{W} = V_{IL}$ transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If $\overline{OE} = VIL$ during a R/\overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If $\overline{OE} = VIH$ during an R/\overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,4)



NOTES:

- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} =VIL and R/ \overline{W} = VIL.
- 3. two is measured from the earlier of \overline{CE} or R/\overline{W} going HIGH to the end-of-write cycle.
- 4. If the $\overline{\text{CE}}$ LOW transition occurs simultaneously with or after the R/\overline{W} LOW transition, the outputs remain in the High-impedance state.
- 5. Timing depends on which enable signal (CE or R/W) is asserted last.

Functional Description

The IDT7134 provides two ports with separate control, address, and I/O pins that permit independent access for reads or writes to any location in memory. These devices have an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into standby mode when not selected ($\overline{\text{CE}}$ HIGH). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control ($\overline{\text{OE}}$). In the read mode, the port's $\overline{\text{OE}}$ turns on the output drivers when set LOW. Non-contention READ/WRITE conditions are illustrated in Truth Table I.

Truth Table I - Read/Write Control

Left or Right Port ⁽¹⁾			Port ⁽¹⁾	
R/W	ΖĒ	Œ	D0-7	Function
Х	Н	Х	Z	Port Deselected and in Power-Down Mode, IsB2 or IsB4
Х	Η	Χ	Z	CER = CEL = H, Power Down Mode IsB1 or IsB3
L	L	Χ	DATAIN	Data on port written into memory
Н	L	Ш	DATAout	Data in memory output on port
Χ	Χ	Н	Z	High impedance outputs

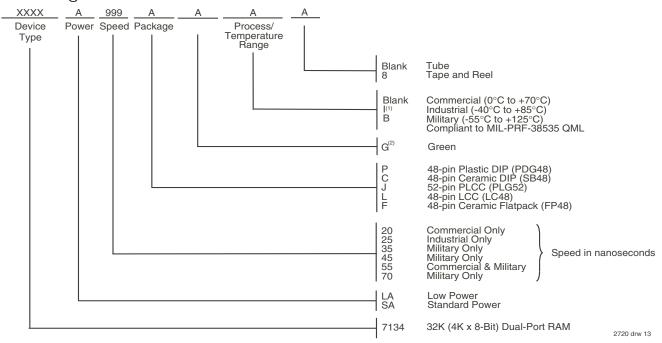
NOTE:

2720 tbl 11

1. $A_{0L} - A_{11L} \neq A_{0R} - A_{11R}$

"H" = VIH, "L" = VIL, "X" = Don't Care, and "Z" = High Impedance

Ordering Information



NOTES:

- 1. Contact your local sales office for industrial temp. range for other speeds, packages and powers.
- Green parts available. For specific speeds, packages and powers contact your local sales office.
 LEAD FINISH (SnPb) parts are Obsolete excluding FP48, LC48 & SB48. Product Discontinuation Notice PDN# SP-17-02
 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
20	7134LA20JG	PLG52	PLCC	С
	7134LA20JG8	PLG52	PLCC	С
	7134LA20PDG	PDG48	PDIP	С
25	7134LA25JGI	PLG52	PLCC	I
	7134LA25JGl8	PLG52	PLCC	I
	7134LA25PDGI	PDG48	PDIP	I
35	7134LA35CB	SB48	SB	М
	7134LA35FB	FP48	FPACK	М
	7134LA35L48B	LC48	LCC	М
45	7134LA45CB	SB48	SB	М
55	7134LA55CB	SB48	SB	М
	7134LA55L48B	LC48	LCC	М
70	7134LA70CB	SB48	SB	М
	7134LA70L48B	LC48	LCC	М

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
35	7134SA35CB	SB48	SB	М
	7134SA35L48B	LC48	LCC	М
45	7134SA45CB	SB48	SB	М
55	7134SA55CB	SB48	SB	М
	7134SA55JG	PLG52	PLCC	С
	7134SA55JG8	PLG52	PLCC	С
	7134SA55L48B	LC48	LCC	М
70	7134SA70CB	SB48	SB	М
	7134SA70L48B	LC48	LCC	М

Datasheet Document History

03/25/99:		Initiated datasheet document history
03/23/99.		Converted to new format
		Cosmetic and typographical corrections
	Dagge 2	
0/0/0/00	Pages 2	Added additional notes to pin configurations
060/9/99:		Changed drawing format
10/01/99:		Added Industrial Temperature Ranges and removed corresponding notes
11/10/99:		Replaced IDT logo
12/22/99:	Page 1	Made corrections to drawing
03/03/00:		Corrected block diagram and pin configurations
		Changed ±500mV to 0mV
01/12/00:	Pages 12	Moved "Description to page 2 and adjusted page layout
	Page 1	Added "LA only)" to paragraph
	Page 2	Fixed P48-1 package description
	Page 3	Increased storage temperature parameters
		Clarified TA parameter
	Page 4	DC Electrical parameters-changed wording from "open" to "disabled"
	Page 10	Fixed Truth Table specification in "Functional Description" paragraph
01/17/06:	Page 1	Added green availability to features
	Page 11	Added green indicator to ordering information
	Page 1 & 11	Replaced old IDT™ with new IDT™ logo
08/12/08:	Page 11	Corrected typo in the ordering information
10/21/08:	Page 11	Removed "IDT" from orderable part number
01/16/13:	Page 1, 4, 6 & 8	Removed Military 25ns & Industrial 35ns speed grades from Features and corrected
	•	the headers of the DC Chars and AC Chars tables to indicate this change
	Page 11	Added T& R indicator to and removed Military 25ns & Industrial 35ns speed grades from the
	ŭ	ordering information
10/21/08:	Page 11	Removed "IDT" from orderable part number
02/04/13:	Page 1, 4, 6 & 8	Removed Military 25ns & Industrial 35ns speed grades from Features and corrected
		the headers of the DC Chars and AC Chars tables to indicate this change
	Page 11	Added T& R indicator to and removed Military 25ns & Industrial 35ns speed grades from the
	3	ordering information
	Page 2	Typo/correction
01/11/18:	3	Product Discontinuation Notice - PDN# SP-17-02
		Last time buy expires June 15, 2018
05/10/21:	Pages 1 - 14	Rebranded as Renesas datasheet
	Page 2 & 3	Rotated LC48 LCC, FP48 Flatpack & PLG52 PLCC to accurately reflect pin 1 orientation
	Page 2, 3 & 12	Updated package codes
	Page 12	Added Orderable Part Information tables
	1 ago 12	. 1885 B. S.

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